

N-channel TrenchMOS standard level FET Rev. 02 — 4 March 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- **1.3 Applications**
 - DC-to-DC convertors

1.4 Quick reference data

Table 4 Quick reference

- Low conduction losses due to low on-state resistance
- Switched-mode power supplies

Table 1.	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	110	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u> and <u>3</u>	-	-	27.6	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	107	W
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 27 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	12	-	nC
Static ch	aracteristics					
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 14 A; T_j = 25 °C; see <u>Figure 9</u> and <u>10</u>	-	40	50	mΩ



N-channel TrenchMOS standard level FET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT78 (TO-220AB)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHP27NQ11T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

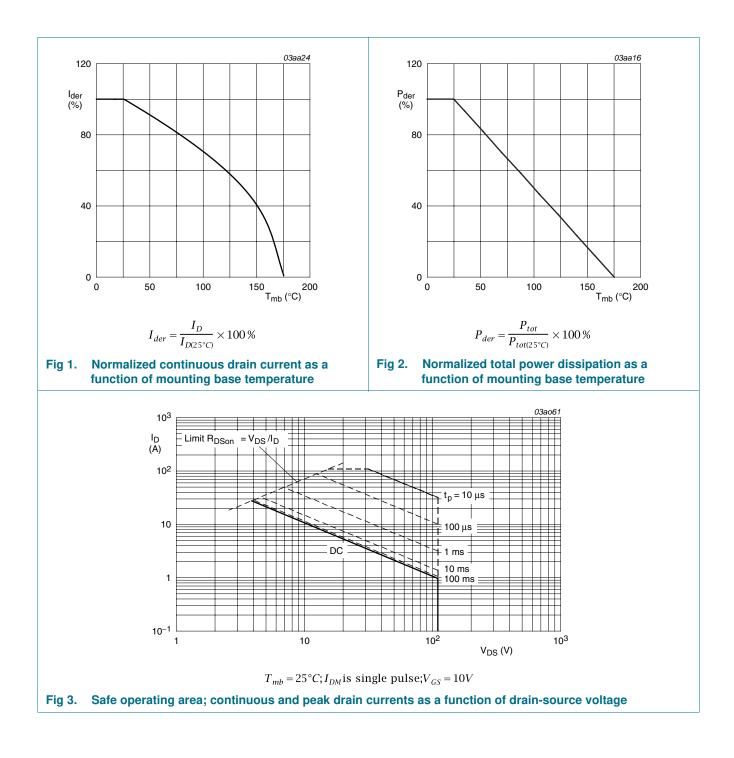
4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	110	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	110	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{1} \text{ and } \frac{3}{2}$	-	27.6	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	20	А
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	112	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	107	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
ls	source current	T _{mb} = 25 °C	-	28	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	112	А
Avalanche	e ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 30 A; V_{sup} ≤ 100 V; unclamped; t_{p} = 0.05 ms; R_{GS} = 50 Ω	-	90	mJ
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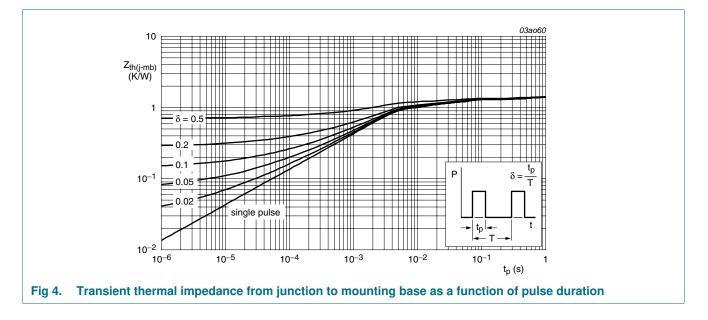
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N-channel TrenchMOS standard level FET

Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	1.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

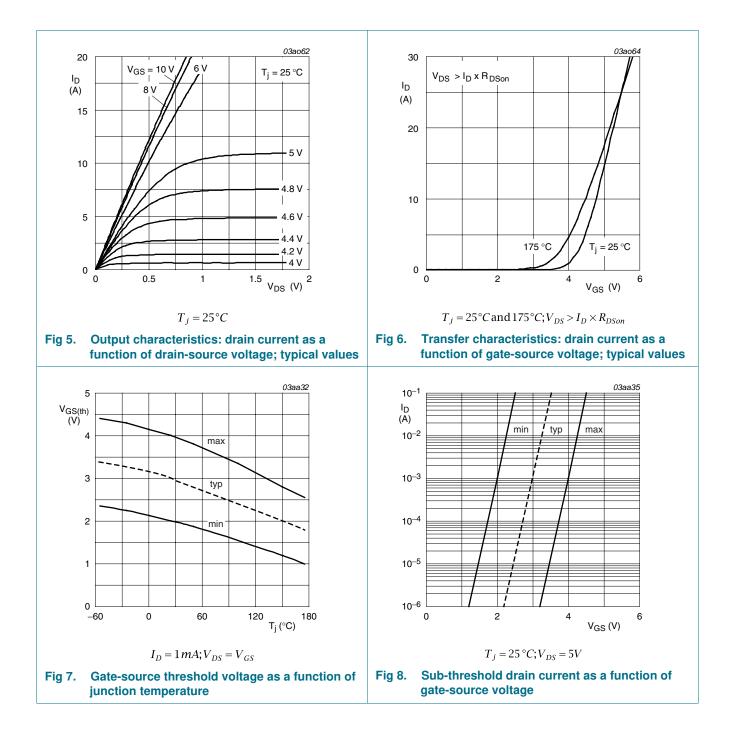


N-channel TrenchMOS standard level FET

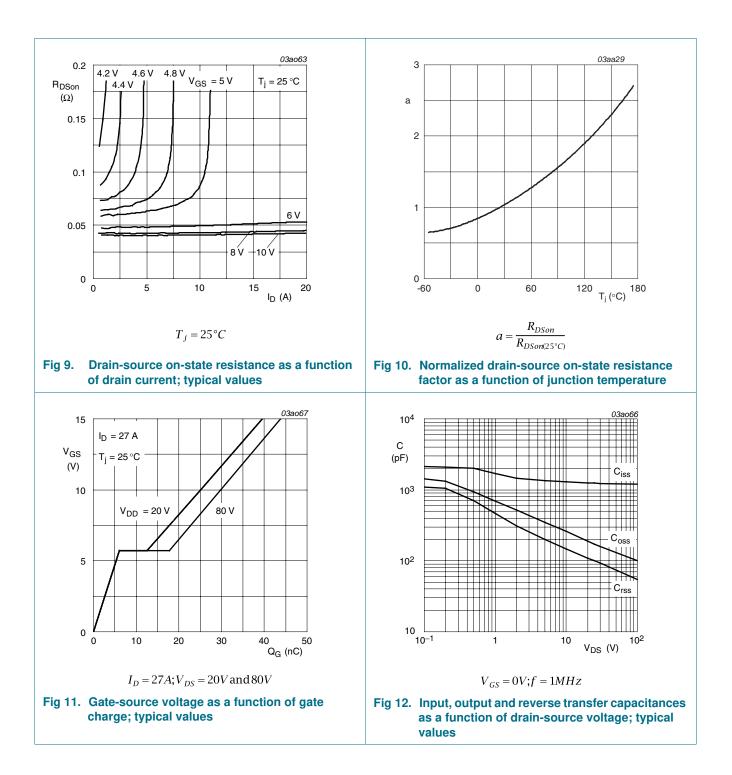
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	99	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	110	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 7 and 8	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 7 and 8	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 7 and 8	-	-	4.4	V
IDSS	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 14 A; T _j = 175 °C; see <u>Figure 9</u> and <u>10</u>	-	-	135	mΩ
		V_{GS} = 10 V; I _D = 14 A; T _j = 25 °C; see <u>Figure 9</u> and <u>10</u>	-	40	50	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 27 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	30	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 11}$	-	6	-	nC
Q _{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;$	-	1240	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 12$	-	170	-	pF
C _{rss}	reverse transfer capacitance		-	100	-	pF
d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C$	-	43	-	ns
t _{d(off)}	turn-off delay time		-	32	-	ns
t _f	fall time		-	24	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 14 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 13	-	0.9	1.5	V
t _{rr}	reverse recovery time	$I_{S} = 14 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s};$	-	60	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C$	-	160	-	nC

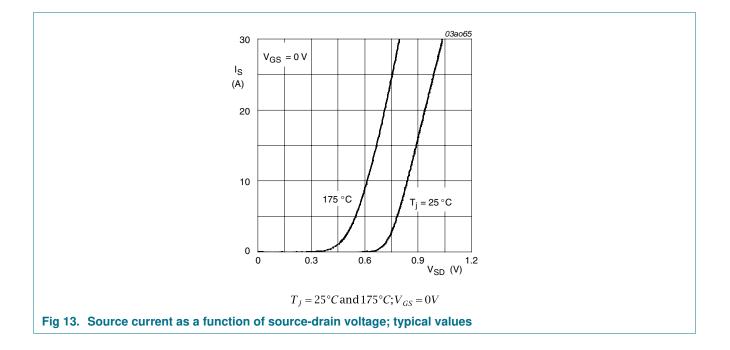
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N-channel TrenchMOS standard level FET

7. Package outline

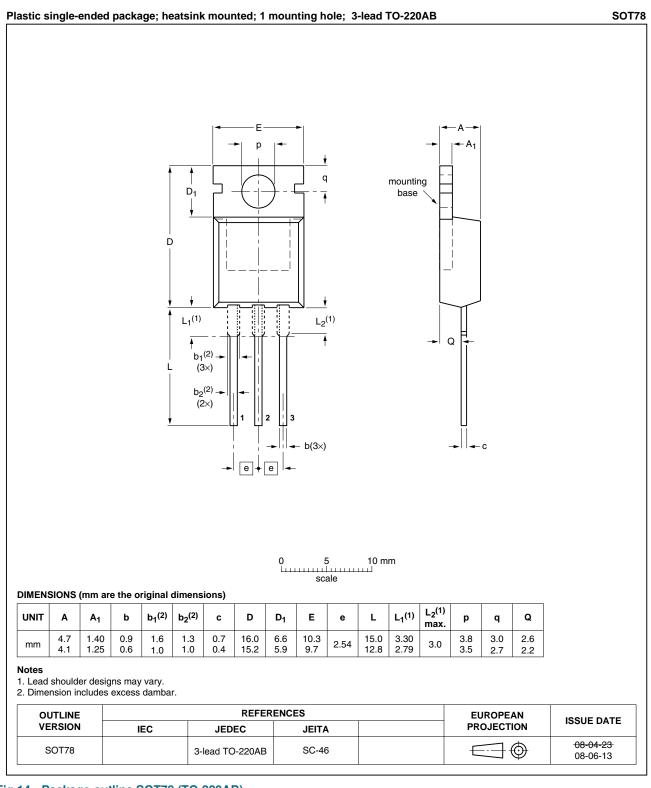


Fig 14. Package outline SOT78 (TO-220AB)

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N-channel TrenchMOS standard level FET

8. Revision history

Table 7. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP27NQ11T_2	20100304	Product data sheet	-	PHP27NQ11T-01
Modifications:		of this data sheet has bee of NXP Semiconductors.	n redesigned to comply	y with the new identity
	 Legal texts 	have been adapted to the	new company name w	here appropriate.
PHP27NQ11T-01 (9397 750 13183)	20040517	Product data	-	-

N-channel TrenchMOS standard level FET

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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N-channel TrenchMOS standard level FET

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12